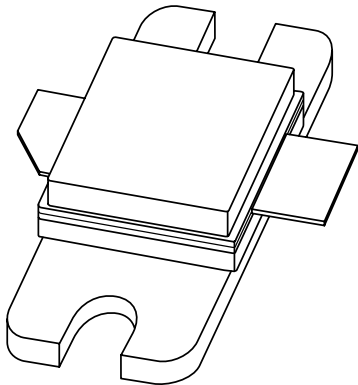


DATA SHEET



BLS3135-50 Microwave power transistor

Product specification
Supersedes data of 1999 Aug 16

2003 Apr 15

Microwave power transistor

BLS3135-50

FEATURES

- Suitable for short and medium pulse applications
- Internal input and output matching networks for an easy circuit design
- Emitter ballasting resistors improve ruggedness
- Gold metallization ensures excellent reliability
- Interdigitated emitter-base structure provides high emitter efficiency
- Multicell geometry improves power sharing and reduces thermal resistance.

APPLICATIONS

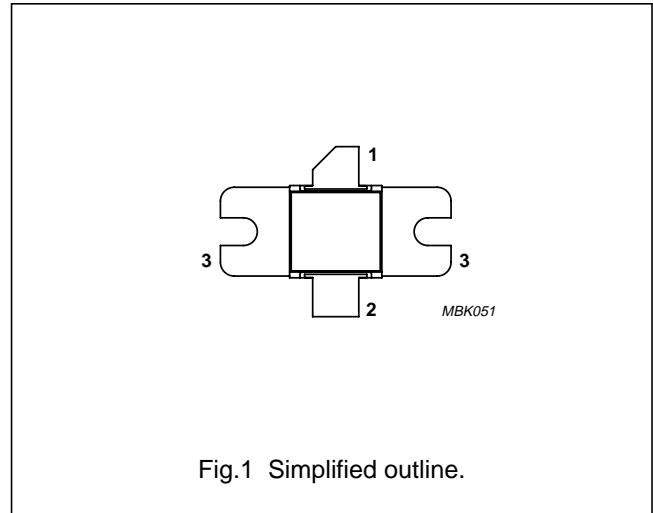
- Common base class-C pulsed power amplifiers for radar applications in the 3.1 to 3.5 GHz band.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a 2-lead rectangular flange package with a ceramic cap (SOT422A) with the common base connected to the flange.

PINNING - SOT422A

PIN	DESCRIPTION
1	collector
2	emitter
3	base; connected to flange



QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ }^\circ\text{C}$ in a common base class-C test circuit.

MODE OF OPERATION	f (GHz)	V_{CB} (V)	P_L (W)	G_p (dB)	η_c (%)
Pulsed, class-C	3.1 to 3.5	40	50	typ. 8	typ. 40

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

Microwave power transistor

BLS3135-50

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	75	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	75	V
V_{EBO}	emitter-base voltage	open collector	–	2	V
I_{CM}	peak collector current	$t_p \leq 100 \mu\text{s}$; $\delta \leq 10\%$	–	6	A
P_{tot}	total power dissipation	$t_p = 100 \mu\text{s}$; $\delta = 10\%$; $T_{mb} = 25 \text{ }^\circ\text{C}$	–	80	W
T_{stg}	storage temperature		–65	+200	$^\circ\text{C}$
T_j	operating junction temperature		–	200	$^\circ\text{C}$
T_{sld}	soldering temperature	up to 0.2 mm from ceramic cap; $t \leq 10 \text{ s}$	–	235	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$Z_{th\ j-h}$	thermal impedance from junction to heatsink	$t_p = 100 \mu\text{s}$; $\delta = 10\%$; note 1	0.71	K/W
		$t_p = 300 \mu\text{s}$; $\delta = 10\%$; note 1	0.99	K/W

Note

1. Equivalent thermal impedance under pulsed microwave operating conditions. Measured with IR-scan with 20 μm spot size at hotspot.

CHARACTERISTICS

 $T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 15 \text{ mA}$; open emitter	75	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 15 \text{ mA}$; $V_{BE} = 0$	75	–	V
I_{CBO}	collector leakage current	$V_{CB} = 40 \text{ V}$; $I_E = 0$	–	1.5	mA
I_{CES}	collector leakage current	$V_{CE} = 40 \text{ V}$; $V_{BE} = 0$	–	3	mA
I_{EBO}	emitter leakage current	$V_{EB} = 1.5 \text{ V}$; $I_C = 0$	–	0.3	mA
h_{FE}	DC current gain	$V_{CB} = 5 \text{ V}$; $I_C = 1.5 \text{ A}$	40	–	

APPLICATION INFORMATION

RF performance at $T_h = 25 \text{ }^\circ\text{C}$ in a common-base test circuit.

MODE OF OPERATION	f (GHz)	V_{CE} (V)	P_L (W)	G_p (dB)	η_c (%)
Class-C; $t_p = 100 \mu\text{s}$; $\delta = 10\%$	3.1 to 3.5	40	≥ 50 typ. 55	≥ 7 typ. 8	≥ 35 typ. 40

Microwave power transistor

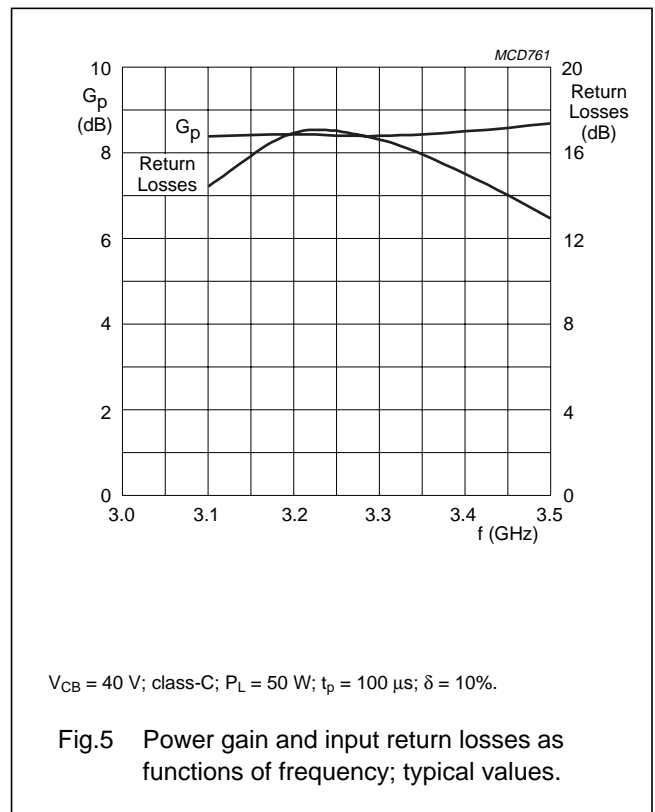
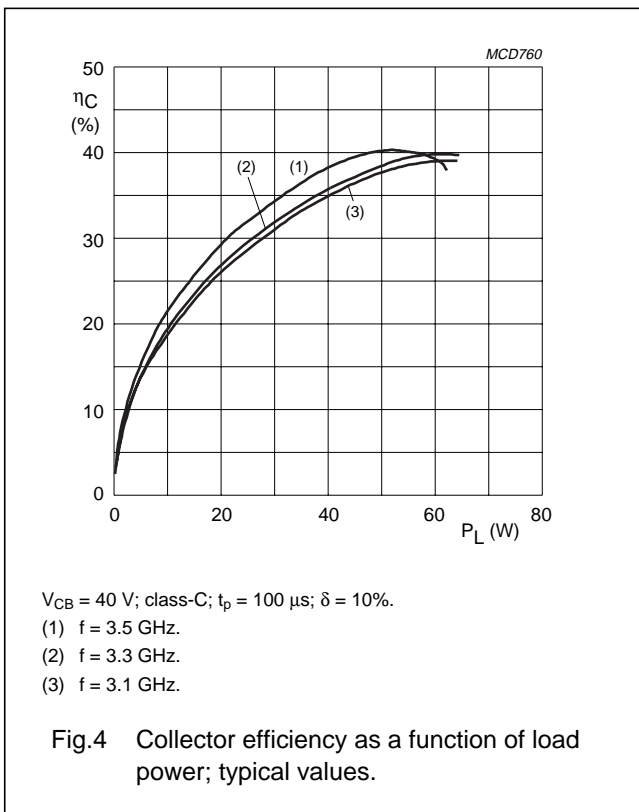
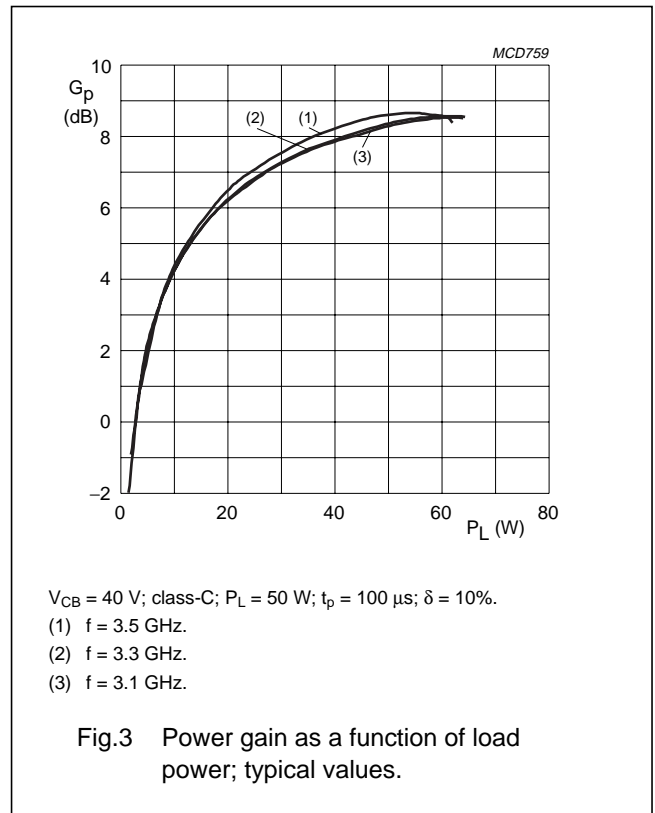
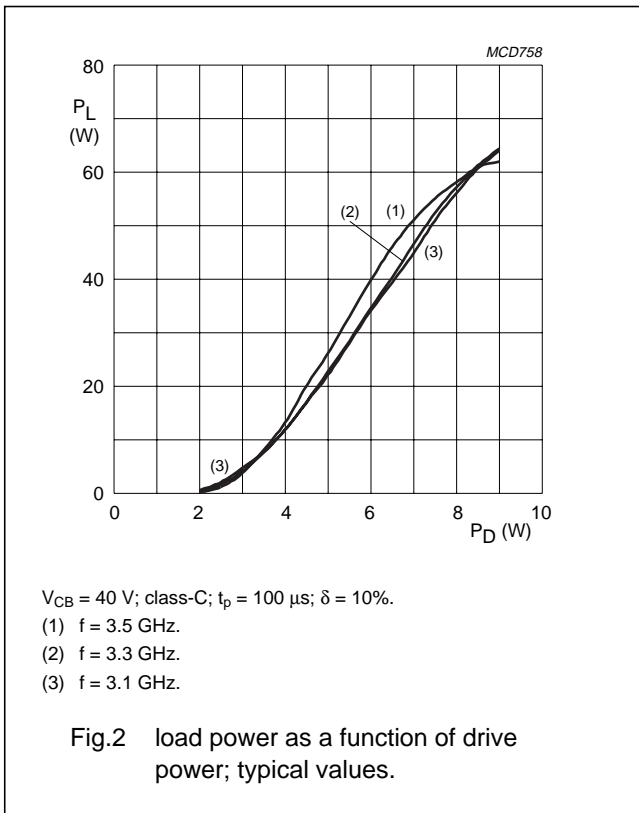
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Typical impedance

FREQUENCY (GHZ)	Z_S (Ω)	Z_L (Ω)
3.1	23.5 - j 5.6	7.8 - j 3.7
3.2	23.6 - j 4.3	7.3 - j 4.1
3.3	23.8 - j 2.9	6.6 - j 4.3
3.4	24.3 - j 1.6	5.8 - j 4.2
3.5	24.9 - j 0.3	5.1 - j 4.1

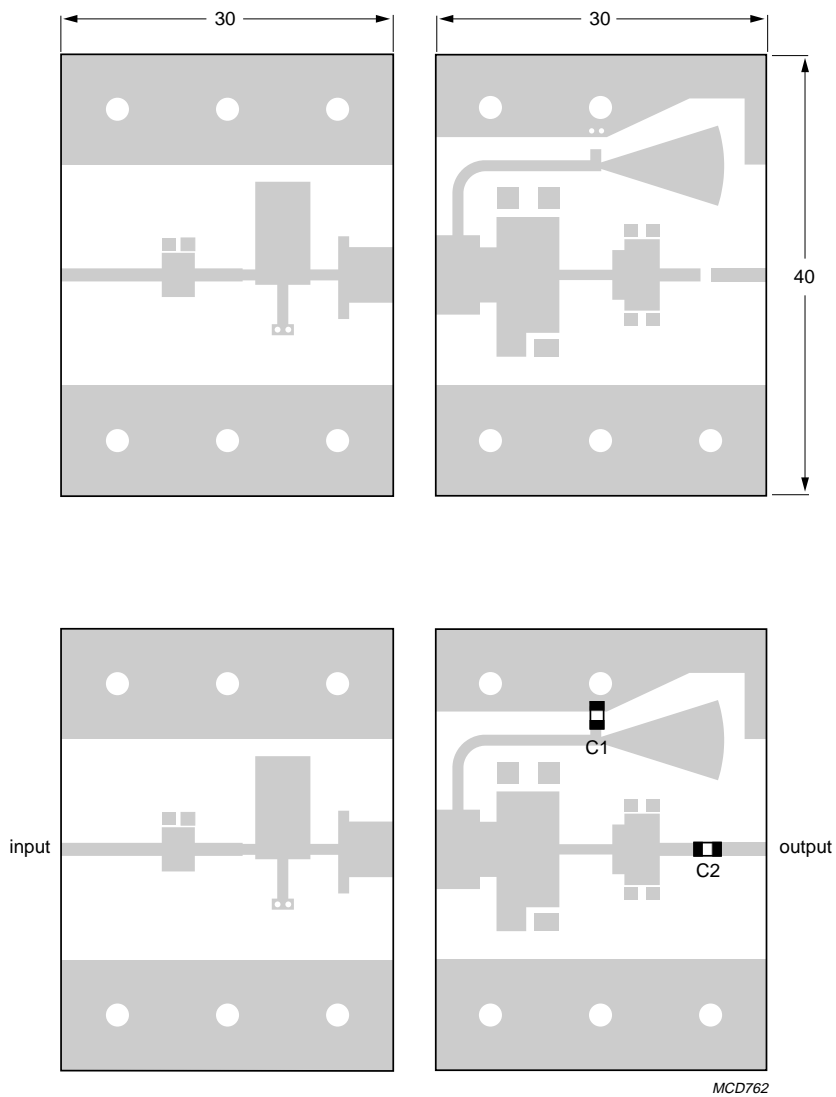
Microwave power transistor

BLS3135-50



Microwave power transistor

BLS3135-50



Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board with Duroid dielectric ($\epsilon_r = 2.2$), thickness 0.38 mm. The other side is unetched and serves as a ground plane.

C1 = C2 = ATC 100A 5.1 pF

Fig.6 Component layout for 3.1 to 3.5 GHz class-C test circuit.

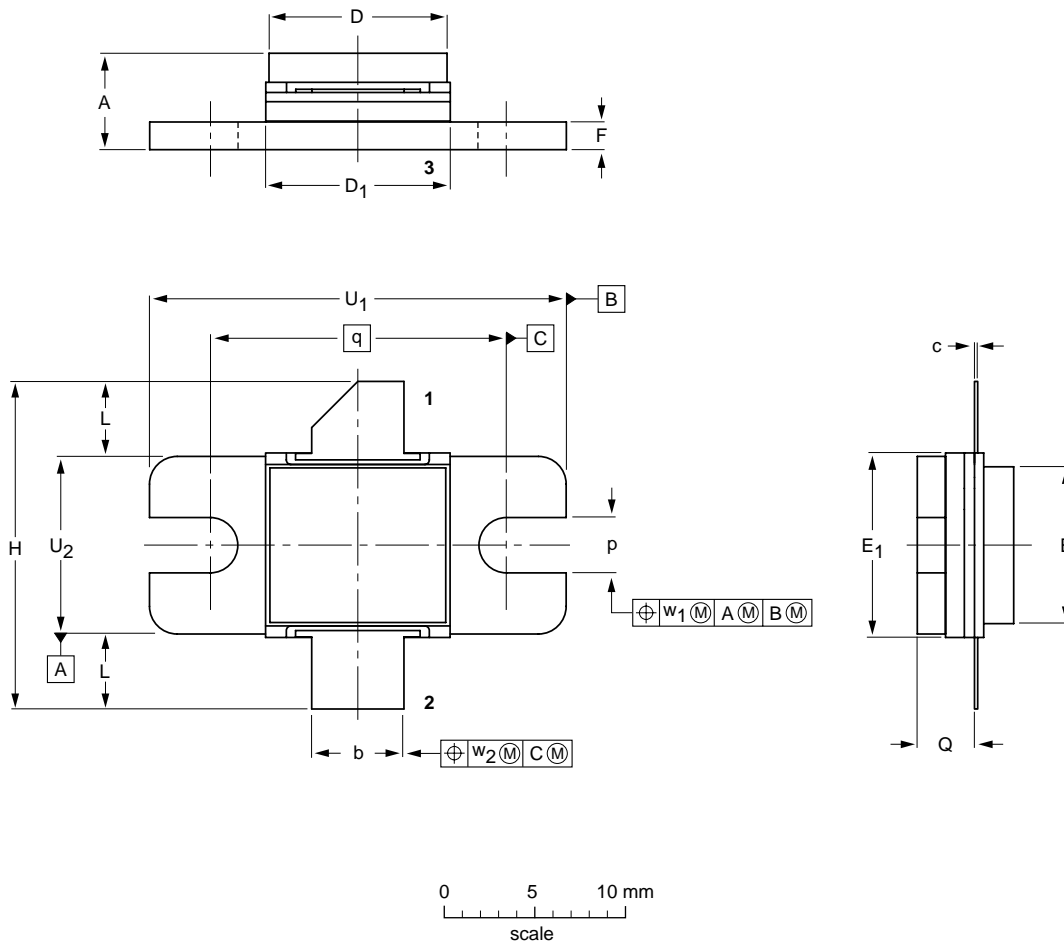
Microwave power transistor

BLS3135-50

PACKAGE OUTLINE

Flanged hermetic ceramic package; 2 mounting holes; 2 leads

SOT422A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	p	Q	q	U ₁	U ₂	w ₁	w ₂
mm	5.72 4.83	5.21 4.95	0.13 0.08	9.93 9.68	10.29 10.03	8.76 8.51	10.29 10.03	1.58 1.47	19.18 17.65	4.52 3.74	3.43 3.18	3.35 2.92	16.51	22.99 22.73	9.91 9.65	0.25	0.76
inches	0.225 0.190	0.205 0.195	0.005 0.003	0.391 0.381	0.405 0.395	0.345 0.335	0.405 0.395	0.062 0.058	0.755 0.695	0.178 0.147	0.135 0.125	0.132 0.115	0.65	0.905 0.895	0.390 0.380	0.01	0.03

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT422A					99-03-29

Microwave power transistor

BLS3135-50

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Microwave power transistor

BLS3135-50

NOTES

Microwave power transistor

BLS3135-50

NOTES

Microwave power transistor

BLS3135-50

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Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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